eGaN® FET DATASHEET EPC2034

EPC2034 – Enhancement Mode Power Transistor

 V_{DS} , 200 V $R_{DS(on)}\,,\,\,10\,m\Omega$ I_D, 48 A









Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low $R_{DS(on)}$, while its lateral device structure and majority carrier diode provide exceptionally low Q_G and zero Q_{RR}. The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.

	Maximum Ratings				
	PARAMETER	VALUE	UNIT		
V _{DS}	Drain-to-Source Voltage (Continuous)	200	V		
	Continuous ($T_A = 25^{\circ}C$, $R_{\theta JA} = 3^{\circ}C/W$)	48	^		
I _D	Pulsed (25°C, T _{PULSE} = 300 μs)	200	Α		
V	Gate-to-Source Voltage	6	V		
V_{GS}	Gate-to-Source Voltage	-4	V		
T _J	Operating Temperature	-40 to 150	۰٫		
T _{STG}	Storage Temperature	-40 to 150	ر		

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(2)	8	9	9	(2)
(3)	(3)	(3)	(3)	(3)
		(2)	(2)	(
(2)	8	6		6
(3)	(2)	(a)	(2)	(3)

EPC2034 eGaN® FETs are supplied only in passivated die form with solder bumps. Die Size: 4.6 mm x 2.6 mm

- High Frequency DC-DC Conversion
- Motor Drive
- Industrial Automation
- · Class-D Audio

	Thermal Characteristics	Thermal Characteristics				
	PARAMETER	TYP	UNIT			
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.45				
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	3.9	°C/W			
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	45				

Note 1: $R_{\theta JA}$ is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board. See https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf for details

Static Characteristics (T _J = 25°C unless otherwise stated)						
PARAMETER TEST CONDITIONS MIN TYP MAX UNIT						UNIT
BV _{DSS}	Drain-to-Source Voltage	$V_{GS} = 0 \text{ V, I}_{D} = 0.6 \text{ mA}$	200			V
I _{DSS}	Drain-Source Leakage	$V_{DS} = 160 \text{ V}, V_{GS} = 0 \text{ V}$		0.1	0.4	mA
I _{GSS}	Gate-to-Source Forward Leakage	$V_{GS} = 5 \text{ V}$		1	7	mA
	Gate-to-Source Reverse Leakage	V _{GS} = -4 V		0.1	0.4	mA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 7 \text{ mA}$	0.8	1.4	2.5	V
R _{DS(on)}	Drain-Source On Resistance	$V_{GS} = 5 \text{ V, I}_{D} = 20 \text{ A}$		7	10	mΩ
V _{SD}	Source-Drain Forward Voltage	$I_S = 0.5 \text{ A}, V_{GS} = 0 \text{ V}$		1.8		V

All measurements were done with substrate connected to source.

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Dynamic Characteristics (T_J = 25 $^{\circ}$ C unless otherwise stated)						
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
C _{ISS}	Input Capacitance			950	1140	
C _{RSS}	Reverse Transfer Capacitance	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$		2.3		
C _{OSS}	Output Capacitance			450	680	pF
C _{OSS(ER)}	Effective Output Capacitance, Energy Related (Note 2)	V 0+- 100V/V 0V		550		
C _{OSS(TR)}	Effective Output Capacitance, Time Related (Note 3)	$V_{DS} = 0 \text{ to } 100 \text{ V}, V_{GS} = 0 \text{ V}$		750]
R_{G}	Gate Resistance			0.5		Ω
Q_{G}	Total Gate Charge	$V_{DS} = 100 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 20 \text{ A}$		8.8	11	
Q_{GS}	Gate to Source Charge			3]
Q_{GD}	Gate to Drain Charge	$V_{DS} = 100 \text{ V, } I_{D} = 20 \text{ A}$		1.8] [
Q _{G(TH)}	Gate Charge at Threshold			2.2		nC
Q _{OSS}	Output Charge	$V_{DS} = 100 \text{ V}, V_{GS} = 0 \text{ V}$		75	113]
Q _{RR}	Source-Drain Recovery Charge			0		

3.0

3.5

4.0

4.5

25°C 125°C

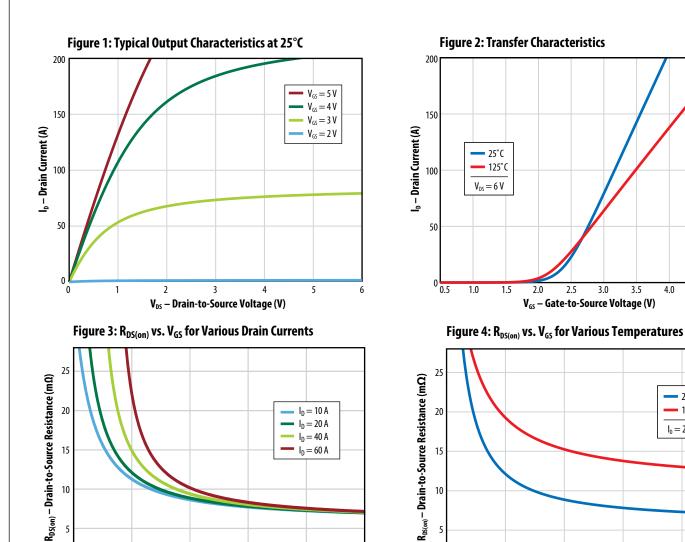
 $I_{D} = 20 \text{ A}$

4.5

5.0

2

Note 2: $C_{OSS(ER)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}. Note 3: $C_{OSS(TR)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 to 50% BV_{DSS}.



5.0

0 L 2.5

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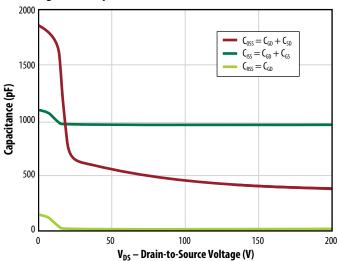


Figure 5b: Capacitance (Log Scale)

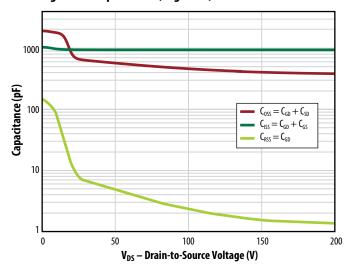


Figure 6: Gate Charge

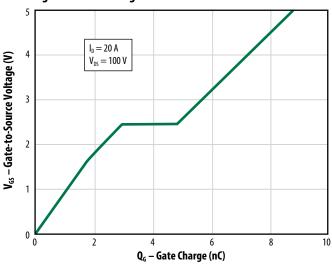


Figure 7: Reverse Drain-Source Characteristics

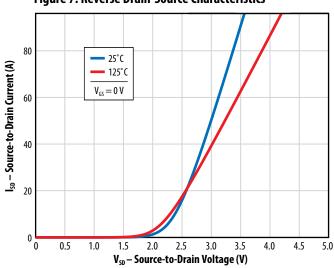


Figure 8: Normalized On-State Resistance vs. Temperature

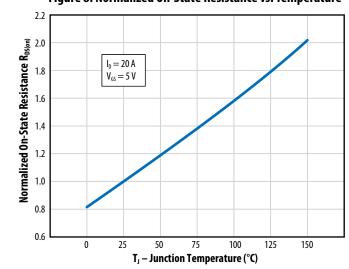
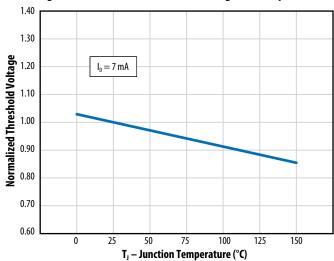


Figure 9: Normalized Threshold Voltage vs. Temperature



All measurements were done with substrate shortened to source. T₁= 25°C unless otherwise stated.

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Figure 10: Gate Leakage Current

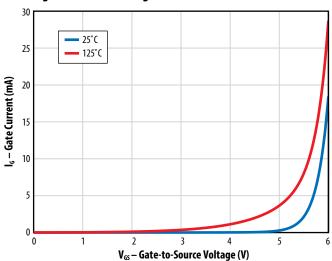


Figure 11: Safe Operating Area

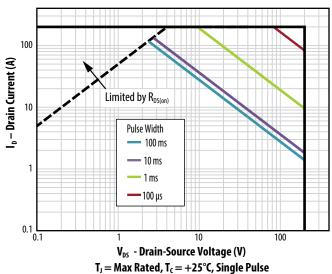
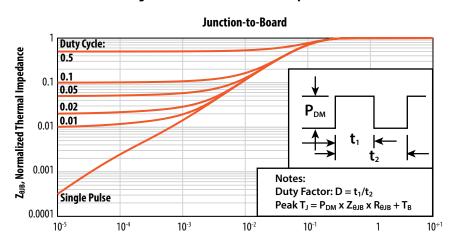
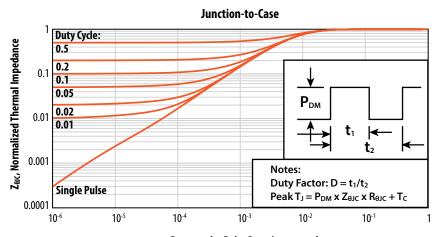


Figure 12: Transient Thermal Response Curves



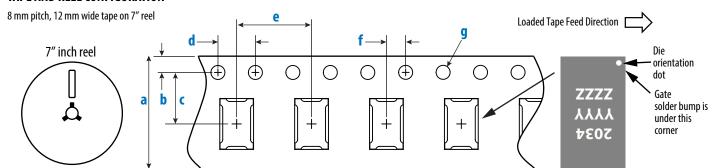
t_p, Rectangular Pulse Duration, seconds



t_p, Rectangular Pulse Duration, seconds

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TAPE AND REEL CONFIGURATION



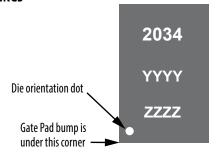
Dimension (mm) **EPC2034 (Note 1)** MIN **Target** 12.00 11.90 12.30 b 1.75 1.65 1.85 5.50 (Note 2) 5.45 5.55 4.00 3.90 4.10 e 8.00 7.90 8.10 2.00 1.95 2.05 f (Note 2) 1.50 1.50 1.60 g

Die is placed into pocket solder bump side down (face side down)

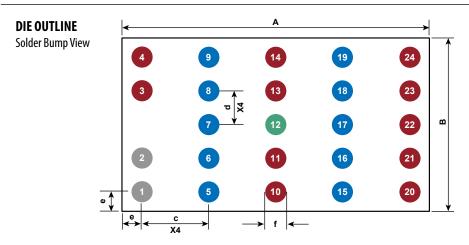
Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/ JEDEC industry standard.

Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

DIE MARKINGS



Dout	Laser Markings				
Part Number	Part # Marking Line 1	Lot_Date Code Marking Line 2	Lot_Date Code Marking Line 3		
EPC2034	2034	YYYY	ZZZZ		



DIM	Micrometers			
DIM	MIN	Nominal	MAX	
Α	4570	4600	4630	
В	2570	2600	2630	
C	1000	1000	1000	
d	500	500	500	
e	285	300	315	
f	332	369	406	

Pads 1 and 2 are Gate;

Pads 5, 6, 7, 8, 9, 15, 16, 17, 18, 19 are Drain;

Pads 3, 4, 10, 11, 13, 14, 20, 21, 22, 23, 24 are Source;

Pad 12 is Substrate*

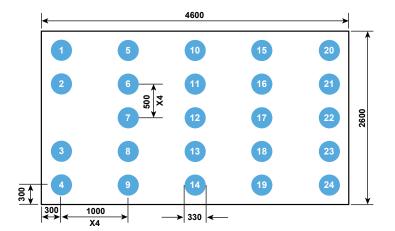
*Substrate pin should be connected to Source

Seating plane Seating plane	280+/-28 S10 typ
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Side View

RECOMMENDED LAND PATTERN

(units in μ m)



Land pattern is solder mask defined Solder mask opening is 330 μm It is recommended to have on-Cu trace PCB vias

Pads 1 and 2 are Gate;

Pads 5, 6, 7, 8, 9, 15, 16, 17, 18, 19 are Drain;

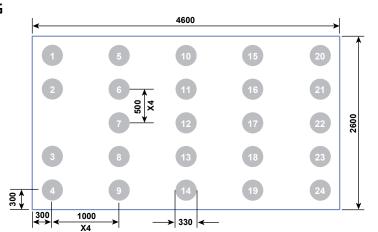
Pads 3, 4, 10, 11, 13, 14, 20, 21, 22, 23, 24 are Source;

Pad 12 is Substrate*

*Substrate pin should be connected to Source

RECOMMENDED STENCIL DRAWING

(units in µm)



Recommended stencil should be 4 mil (100 μ m) thick, must be laser cut, openings per drawing.

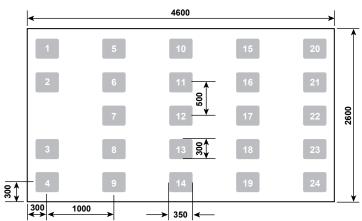
Additional assembly resources available at https://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx

RECOMMENDED STENCIL DRAWING

(units in µm)

Option 2: Intended for use with SAC305 Type 3 solder.

Option 1: Intended for use with SAC305 Type 4 solder.



Recommended stencil should be 4 mil (100 μ m) thick, must be laser cut, openings per drawing.

Additional assembly resources available at https://epc-co.com/epc/DesignSupport/AssemblyBasics.aspx eGaN® FET DATASHEET EPC2034

Errata - EPC2034

Introduction:

This document describes errata to the EPC2034 eGaN® FET and its datasheet. This document should be used in conjunction with the datasheet and may include updates to the specifications that supersede those stated in the EPC2034 datasheet. Errata may cause a product's behavior to deviate from published specifications.

Errata List:

Input Voltage Clarifications

In the Maximum Ratings table, Maximum V_{DS} is specified at 200 V. For applications purposes, the main input DC supply voltage should be limited to 160 V_{DC} . For transient operation between 160 V and 200 V, please contact EPC at Steve.Colino@epc-co.com

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